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via network can thus be obtained for any suitable value of electrical resistance by utilizing the present invention novel method.

In The Claims

Claim 2 has been amended as follows:

X

2. (Amended) An electronic structure having in-situ formed unit resistors according to claim 1, wherein said preprocessed substrate is a semiconductor wafer.

REMARKS

Thorough examination and careful review of the application by the Examiner is noted and appreciated. The gracious allowance of claims 1 and 3-14 are further acknowledged and appreciated.

Claims 2 and 26-33 are rejected. The Applicants hereby affirm an election made by the Applicants' representative during a January 11, 2001 telephone conversation with the Examiner for the prosecution of Group I invention, claims 1-15 and 26-33.